

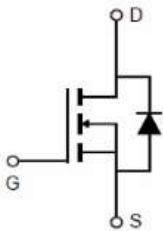
# MJ N-Channel Enhancement Mode Power MOSFET

## Description

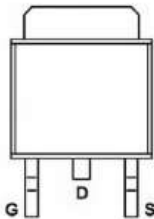
The MJ4030K uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge .  
The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

## General Features

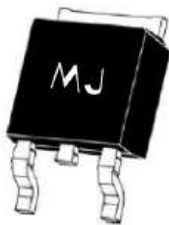
- ◆ **N-Channel**  
 $V_{DS}=40V, I_D=30A$   
 $R_{DS(ON)} < 16m\Omega @ V_{GS}=10V$   
 $R_{DS(ON)} < 24m\Omega @ V_{GS}=4.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package



Schematic diagram



Marking and pin assignment



TO-252-2L top view

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJ4030K	MJ4030K	TO-252-2L	-	-	-

## Absolute Maximum Ratings (Tc =25 °Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	30	A
Drain Current-Continuous( $T_c=100^{\circ}C$ )	$I_{D(100^{\circ}C)}$	21.2	A
Pulsed Drain Current	$I_{DM}$	70	A
Maximum Power Dissipation	$P_D$	45	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

## Thermal Characteristic

Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	3.3	°C/W
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N-CH Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	-	12.3	16	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	-	17	24	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V,I <sub>D</sub> =15A	-	15	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V F=1.0MHz	-	964	-	PF
Output Capacitance	C <sub>Oss</sub>		-	109	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	96	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, R <sub>L</sub> =1.3Ω V <sub>GS</sub> =10V,R <sub>GEN</sub> =3Ω	-	5.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	14	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	24	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V,I <sub>D</sub> =15A V <sub>GS</sub> =10V	-	22.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	5.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =15A	-	0.8	1.2	V

# N- Channel Typical Electrical and Thermal Characteristics (Curves)

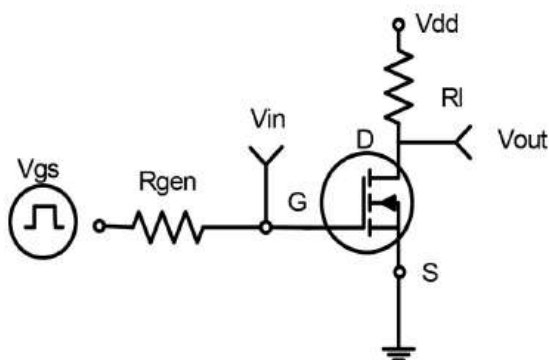


Figure 1 Switching Test Circuit

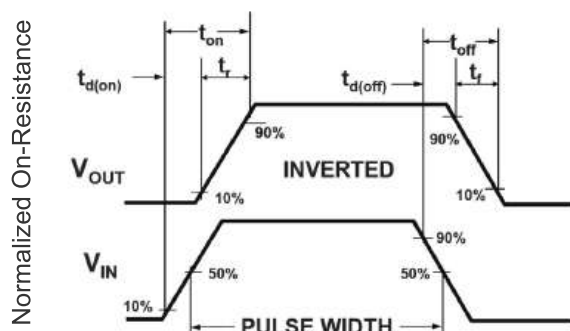


Figure 2 Switching Waveforms

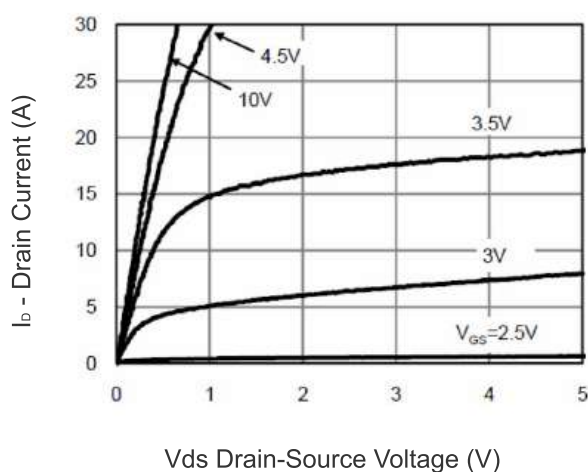


Figure 3 Output Characteristics

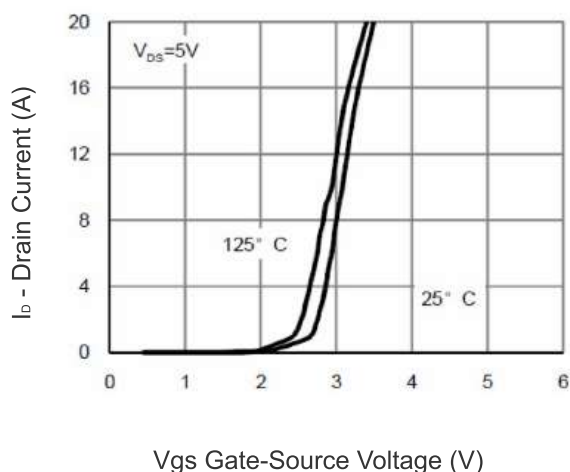


Figure 4 Transfer Characteristics

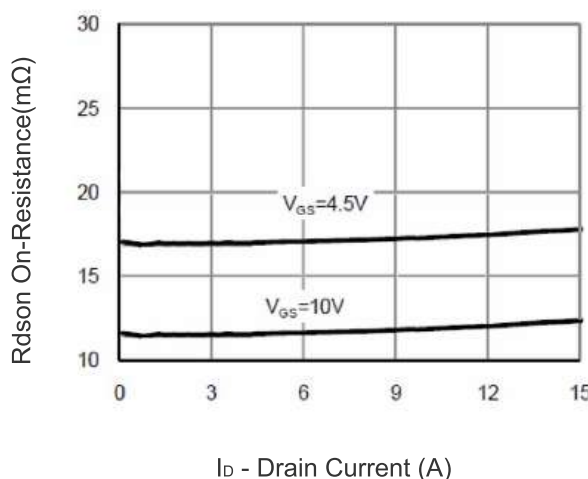


Figure 5 Drain-Source On-Resistance

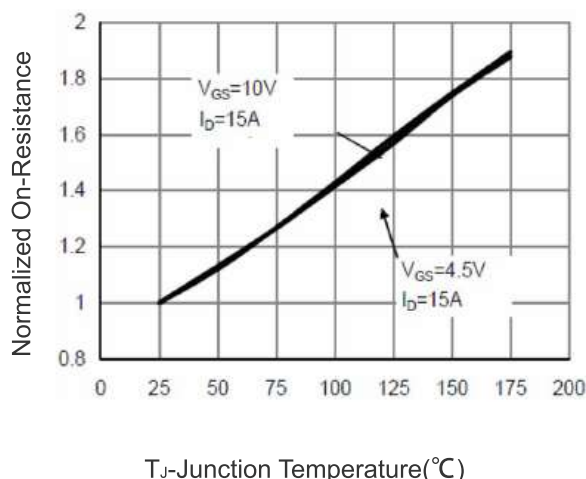
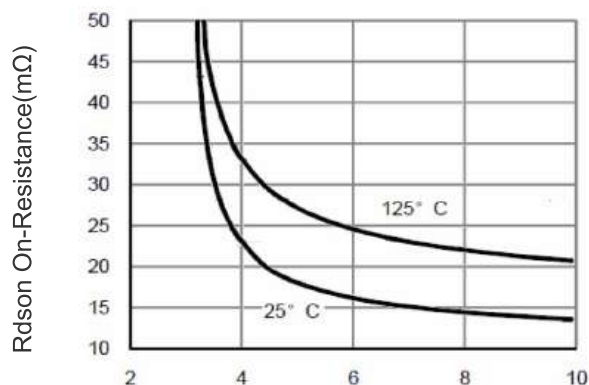
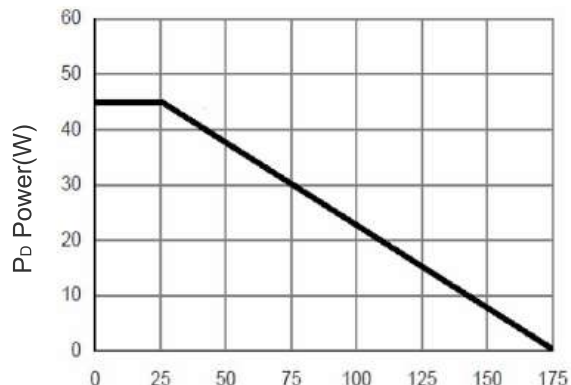


Figure 6 Drain-Source On-Resistance



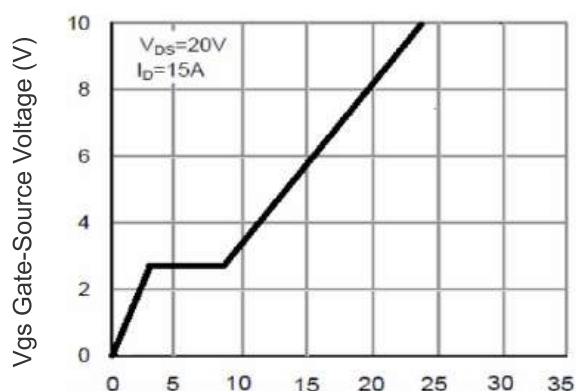
Vgs Gate-Source Voltage (V)

Figure7 Rdson vs Vgs



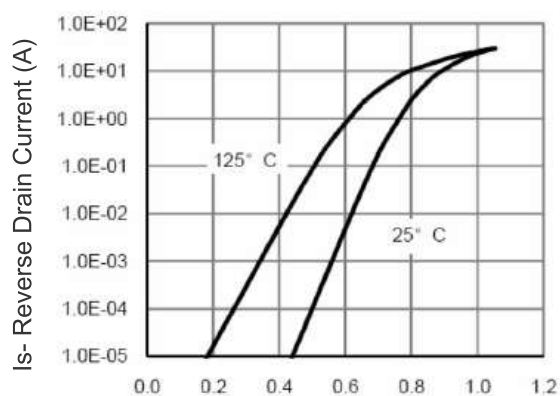
Tj-Junction Temperature(°C)

Figure 8 Power Dissipation



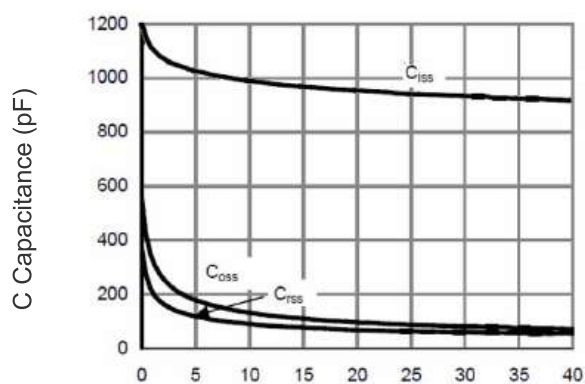
Qg Gate Charge (nC)

Figure 9 Gate Charge



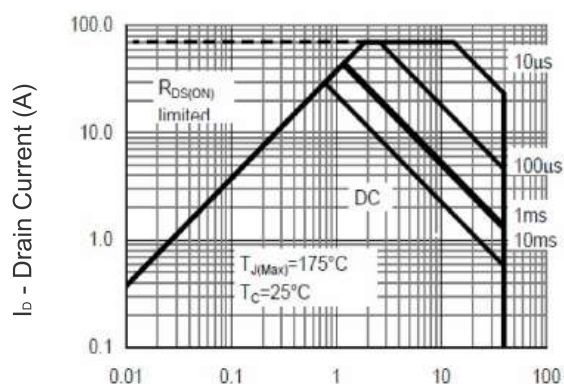
Vds Drain-Source Voltage (V)

Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)

Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area

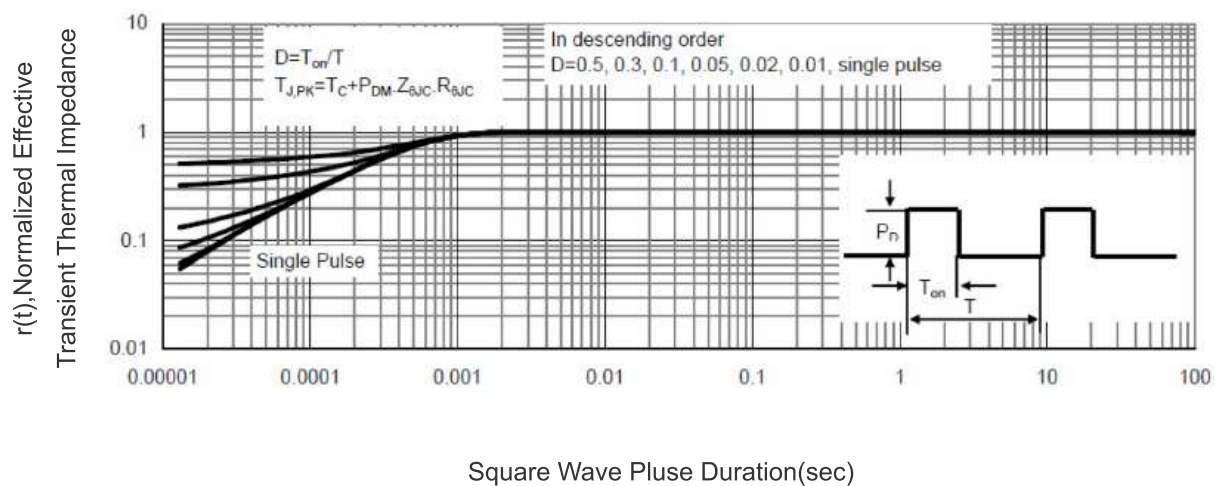
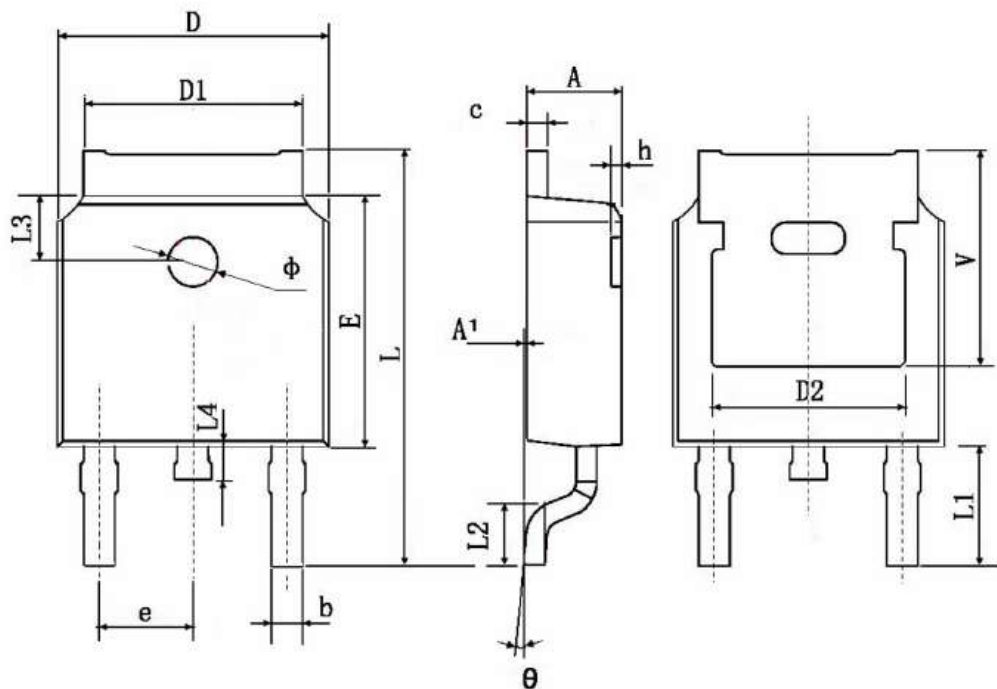


Figure 13 Normalized Maximum Transient Thermal Impedance

# TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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